IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Tikashi AKATSU et al.

Application No:

Group Art Unit:

Filing Date: Concurrently herewith

Examiner:

WAFER WITH A RELAXED USEFUL LAYER AND METHOD OF FORMING THE

Attorney Docket No.: 4717-8900

WAFER

INFORMATION DISCLOSURE STATEMENT

MS PATENT APPLICATION

Commissioner for Patents P.O. Box 1450 Arlexandria, Virginia 22313-1450

Sir:

Pursuant to Applicant's duty of disclosure under 37 C.F.R. § 1.56, enclosed are copies of Nine (9) references listed on the enclosed Form PTO-1449 for the Examiner's review. Also enclosed is a copy of the International Search Report from the corresponding foreign application on which the references were cited.

It is respectfully requested that the references be made of record in this application by the Examiner's completion and return of the attached Form PTO-1449.

No fee is believed to be due for the submission of the references. Should any fees be required, however, please charge such fees to Winston & Strawn Deposit Account No. 50-1814. A copy of this sheet is enclosed for accounting purposes.

Respectfully submitted,

Sept. 17, 2003

E. Bradley Gould

(Reg. No. 41,792)

For: Alan A. Fanucci

(Reg. No. 30,256)

WINSTON & STRAWN Customer No. 28765

202-371-5771

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Form PTO-1449 (Use several sheets if necessary) Sheet 1 of 1					4717-8900 APPLICANT:		L		
					Tukeshi AKATSU, et al. FILING DATE: GROUP:				
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			U.S. PAT	TENT DOC	JMENTS				
*EXAMINER INITIAL	CITE NO.	DOCUMENT NUMBER	DATE	NAME		CLASS	SUBCLASS	FILING I APPROP	
		US 2002/0185686 A1	12/2002	Christianse	n et al.	257	347		
		US 2002/0072130 A1	06/2002	Cheng et al.		438	10		
		US 2001/0003269	06/2001	Wu et al.		117	94		
		6,064,081	05/2000	Robinson		257	183		
		5,461,243	10/1995	Ek et al.		257	190		
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			FOREIGN	PATENT D	OCUMENTS				
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		OTHER REFERE	NCES (Inclu	ding Author,	Title, Date, Pertinent	Pages, Etc	.)		
H. Trinkaus, Strain relaxation mechanism for hydrogen-implanted Si _{1-x} Ge _x /Si(100) heterostructures, 12 June 2000, pp. 3552-54.									
		B. Holländer, Strain relaxation of pseudomorphic $Si_{1-x}Ge_x/Si(100)$ heterostructures after hydrogen or helium ion implantation for virtual substrate fabrication, 2001, pp. 357-67.							
		B. Holländer, Substrate Engineering by Hydrogen or Helium Implantation for Epitaxial Growth of Lattice Mismatched Si _{1-x} Ge _x Films on Silicon, 2000, pp. 326-29.							
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EXAMIN	NER			DAT	E CONSIDERED				
*EXAMIN		Initial if reference considered				9. Draw line	through cit	ation if	not in
conformance and not considered. Include copy of this form with next communication to applicant.									